

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	2	SiOC and copper and amine and etchant and mask	USPAT	OR	OFF	2004/12/14 15:17
L2	603	(134/1.3).CCLS.	USPAT	OR	OFF	2004/12/14 15:17
L3	208	2 and rinse	USPAT	OR	OFF	2004/12/14 15:17
L4	24	2 and etch and ash	USPAT	OR	OFF	2004/12/14 15:17
L5	153	amine and etch and ash and pH	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18
L6	723	photoresist and mask and etch and ash	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18
L7	326	photoresist and mask and etch and ash and copper	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18
L8	145	photoresist and mask and etch and ash and copper and residue	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT	OR	OFF	2004/12/14 15:18
S1	368	(438/689).CCLS.	USPAT	OR	OFF	2004/12/09 14:03
S2	0	S1 and (alkaline adj stripper)	USPAT	OR	OFF	2004/12/09 14:05
S3	25	S1 and (alkaline)	USPAT	OR	OFF	2004/12/09 14:07
S4	7	S1 and (alkaline) and (silicon adj oxide)	USPAT	OR	OFF	2004/12/09 16:03
S5	383	SiOC	USPAT	OR	OFF	2004/12/09 16:03
S6	0	SiOC and (alkaline adj etchant)	USPAT	OR	OFF	2004/12/09 16:03
S7	278	(alkaline adj etchant)	USPAT	OR	OFF	2004/12/09 16:03
S8	43	(alkaline adj etchant) and insulating and dielectric	USPAT	OR	OFF	2004/12/09 16:05
S9	6	(alkaline adj etchant) and insulating and (low adj dielectric)	USPAT	OR	OFF	2004/12/09 16:11
S10	2	SiOC and copper and amine and etchant	USPAT	OR	OFF	2004/12/14 14:46